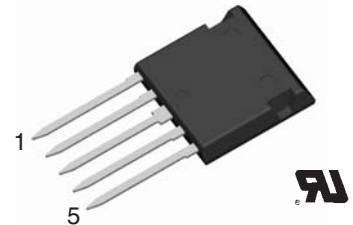
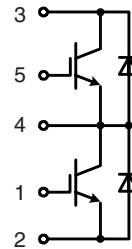


# NPT<sup>3</sup> IGBT

Phaseleg Topology  
in ISOPLUS i4-PAC™

**I<sub>C25</sub> = 33 A**  
**V<sub>CES</sub> = 1200 V**  
**V<sub>CE(sat)typ</sub> = 2.4 V**



## IGBTs

Symbol	Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>VJ</sub> = 25°C to 150°C	1200	V
V <sub>GES</sub>		± 20	V
I <sub>C25</sub>	T <sub>C</sub> = 25°C	33	A
I <sub>C90</sub>	T <sub>C</sub> = 90°C	20	A
I <sub>CM</sub> V <sub>CEK</sub>	V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω; T <sub>VJ</sub> = 125°C RBSOA, Clamped inductive load; L = 100 μH	40	A
		V <sub>CES</sub>	
t <sub>SC</sub> (SCSOA)	V <sub>CE</sub> = 900V; V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω; T <sub>VJ</sub> = 125°C non-repetitive	10	μs
P <sub>tot</sub>	T <sub>C</sub> = 25°C	150	W

## Features

- NPT<sup>3</sup> IGBT
  - positive temperature coefficient of saturation voltage for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- HiPerFRED™ diode
  - fast reverse recovery
  - low operating forward voltage
  - low leakage current
- ISOPLUS i4-PAC™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - enlarged creepage towards heatsink
  - application friendly pinout
  - low inductive current path
  - high reliability
  - industry standard outline
  - UL registered, E 72873

Symbol	Conditions	Characteristic Values (T <sub>VJ</sub> = 25°C, unless otherwise specified)			
		min.	typ.	max.	
V <sub>CE(sat)</sub>	I <sub>C</sub> = 20 A; V <sub>GE</sub> = 15 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		2.4 2.8	V V	
V <sub>GE(th)</sub>	I <sub>C</sub> = 0.6 mA; V <sub>GE</sub> = V <sub>CE</sub>	4.5		6.5 V	
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>GE</sub> = 0 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C		0.2	0.2 mA mA	
I <sub>GES</sub>	V <sub>CE</sub> = 0 V; V <sub>GE</sub> = ± 20 V			200 nA	
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub>	Inductive load, T <sub>VJ</sub> = 125°C V <sub>CE</sub> = 600 V; I <sub>C</sub> = 20 A V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 68 Ω		205 105 320 175 4.1 1.5	ns ns ns ns mJ mJ	
C <sub>ies</sub>		V <sub>CE</sub> = 25 V; V <sub>GE</sub> = 0 V; f = 1 MHz		1.2	nF
Q <sub>Gon</sub>		V <sub>CE</sub> = 600 V; V <sub>GE</sub> = 15 V; I <sub>C</sub> = 20 A		100	nC
R <sub>thJC</sub> R <sub>thJH</sub>		with heat transfer paste		1.2	0.8 K/W K/W

## Applications

- single phaseleg
  - buck-boost chopper
- H bridge
  - power supplies
  - induction heating
  - four quadrant DC drives
  - controlled rectifier
- three phase bridge
  - AC drives
  - controlled rectifier

**Diodes**

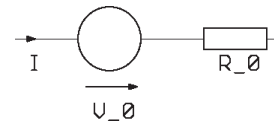
Symbol	Conditions	Maximum Ratings	
$I_{F25}$	$T_C = 25^\circ\text{C}$	25	A
$I_{F90}$	$T_C = 90^\circ\text{C}$	15	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$V_F$	$I_F = 20\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5 1.9	3.0	V V
$I_{RM}$ $t_{rr}$	$I_F = 15\text{ A}; di_F/dt = -400\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	16		A
		130		ns
$R_{thJC}$ $R_{thCH}$	(per diode) with heat transfer paste	3.6		2.3 K/W K/W

**Component**

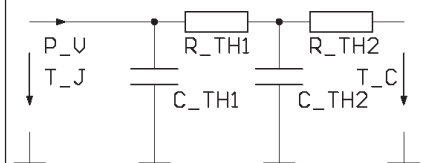
Symbol	Conditions	Maximum Ratings	
$T_{VJ}$		-55...+150	$^\circ\text{C}$
$T_{stg}$		-55...+125	$^\circ\text{C}$
$V_{ISOL}$	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
$F_C$	mounting force with clip	20...120	N

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$C_p$	coupling capacity between shorted pins and mounting tab in the case		40	pF
$d_S, d_A$	pin - pin	1.7		mm
$d_S, d_A$	pin - backside metal	5.5		mm
Weight		9		g

**Equivalent Circuits for Simulation**
**Conduction**


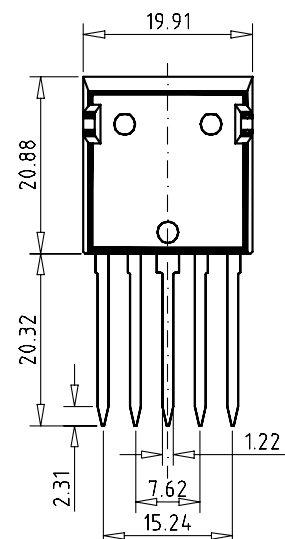
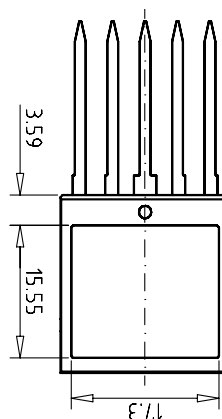
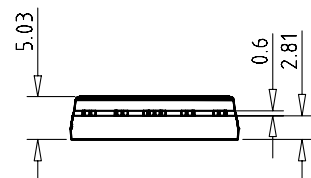
IGBT (typ. at  $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$ )  
 $V_o = 1.09\text{ V}; R_o = 85\text{ m}\Omega$

Free Wheeling Diode (typ. at  $T_J = 125^\circ\text{C}$ )  
 $V_o = 1.3\text{ V}; R_o = 32\text{ m}\Omega$

**Thermal Response**


IGBT (typ.)  
 $C_{th1} = 0.049\text{ J/K}; R_{th1} = 0.15\text{ K/W}$   
 $C_{th2} = 0.133\text{ J/K}; R_{th2} = 0.65\text{ K/W}$

Free Wheeling Diode (typ.)  
 $C_{th1} = 0.021\text{ J/K}; R_{th1} = 0.63\text{ K/W}$   
 $C_{th2} = 0.052\text{ J/K}; R_{th2} = 1.67\text{ K/W}$

**Dimensions in mm (1 mm = 0.0394")**


IXYS reserves the right to change limits, test conditions and dimensions.

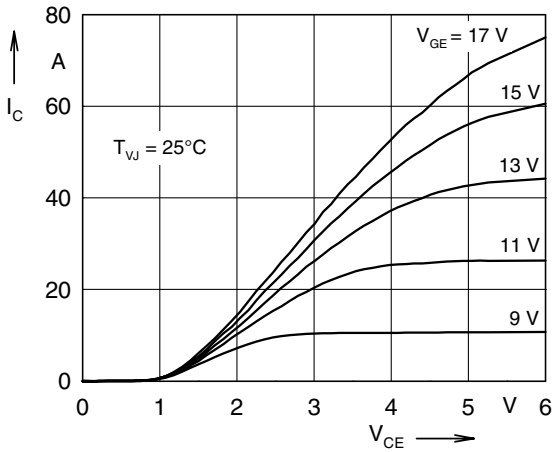


Fig. 1 Typ. output characteristics

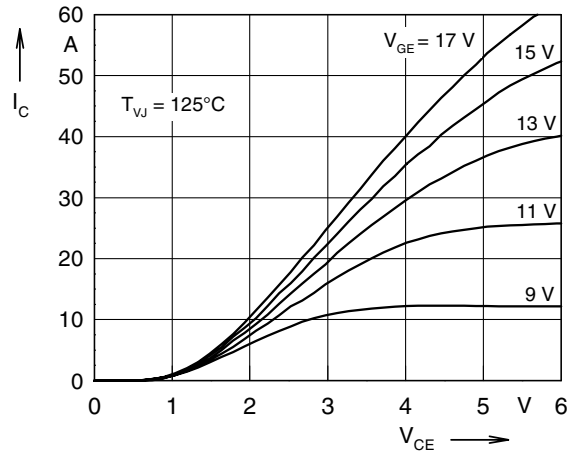


Fig. 2 Typ. output characteristics

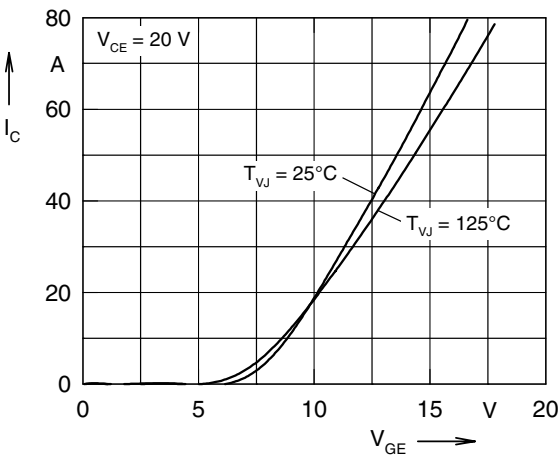


Fig. 3 Typ. transfer characteristics

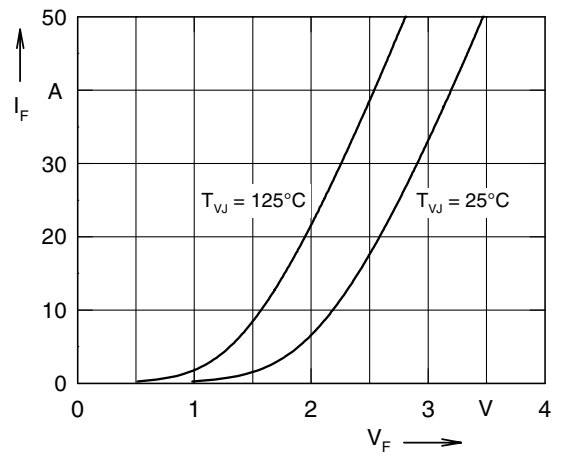


Fig. 4 Typ. forward characteristics of free wheeling diode

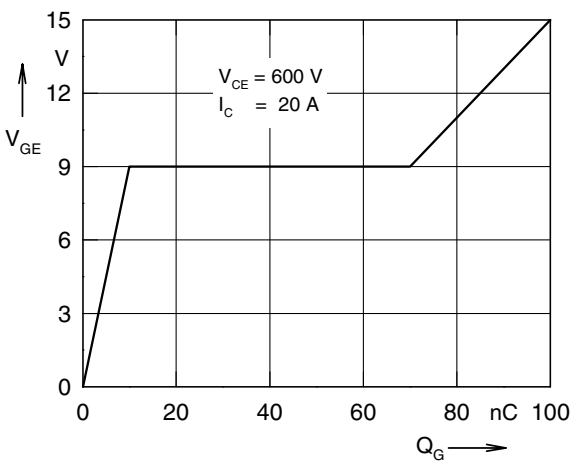


Fig. 5 Typ. turn on gate charge

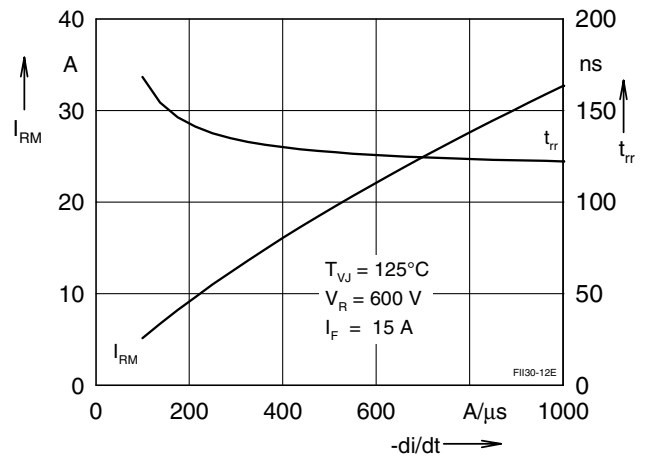


Fig. 6 Typ. turn off characteristics of free wheeling diode

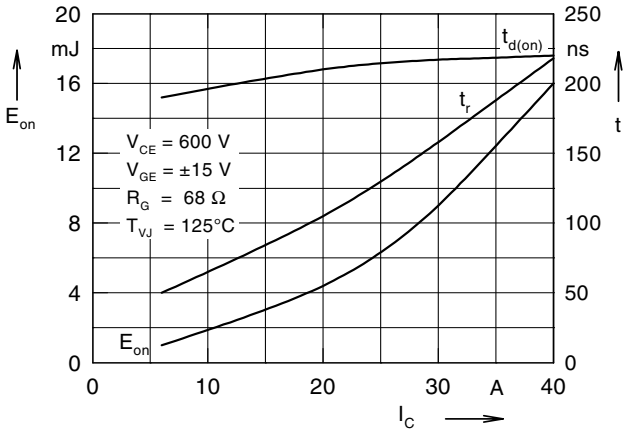


Fig. 7 Typ. turn on energy and switching times versus collector current

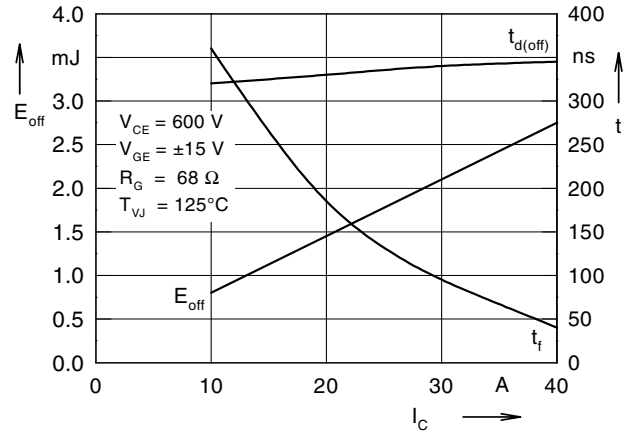


Fig. 8 Typ. turn off energy and switching times versus collector current

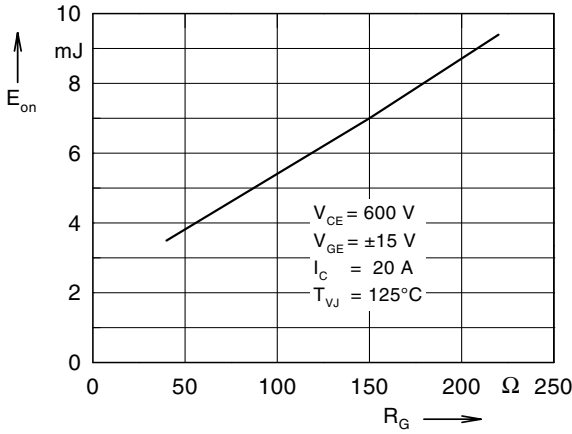


Fig. 9 Typ. turn on energy vs gate resistor

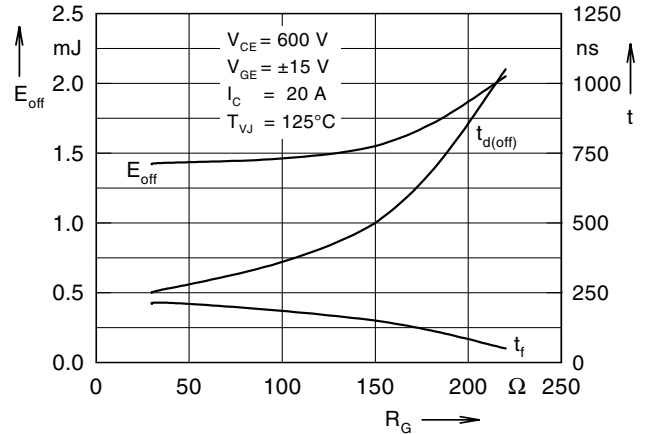


Fig.10 Typ. turn off energy and switching times versus gate resistor

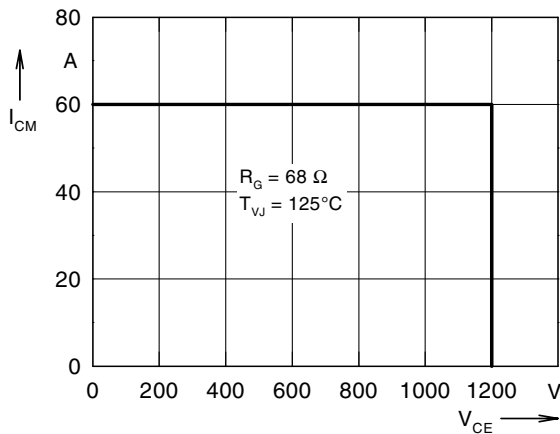


Fig. 11 Reverse biased safe operating area RBSOA

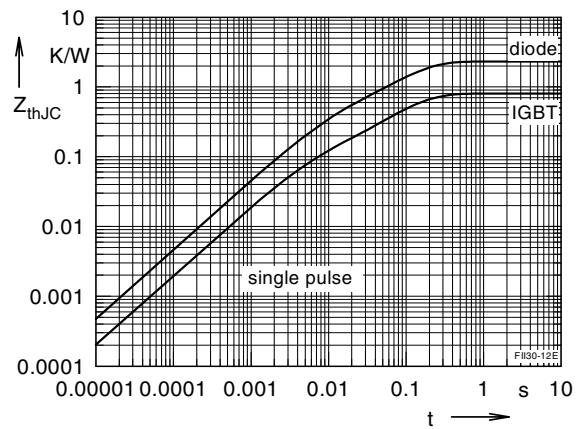


Fig. 12 Typ. transient thermal impedance